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PATENTS, TRADEMARKS,  
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Commissioner of Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Re: Patent No. : US 7,790,569 B2  
Issued : September 7, 2010  
Title : PRODUCTION OF SEMICONDUCTOR  
SUBSTRATES WITH BURIED LAYERS BY  
JOINING (BONDING) SEMICONDUCTOR  
WAFERS  
Docket No. : LEO 003 PA

Sir:

When the printed patent was compared with the attorneys' file copy, the following errors were noted:

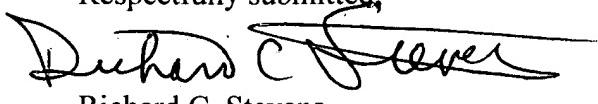
Col. 2, line 59, "this diameter is also to taken in the" should read --this diameter is also to be taken in the--;

Col. 2, line 66, "which result in an transfer of structures" should read --which result in a transfer of structures--;

Col. 4, line 33 , "wafer structure of to bonded wafers" should read --wafer structure of bonded wafers--.

It is thought that these errors are not of material importance, and accordingly no certificate of correction is being requested. It is merely asked that this correspondence be placed of record in the file as calling attention to these errors.

Respectfully submitted,

  
Richard C. Stevens  
Reg. No. 28,046

/vlc